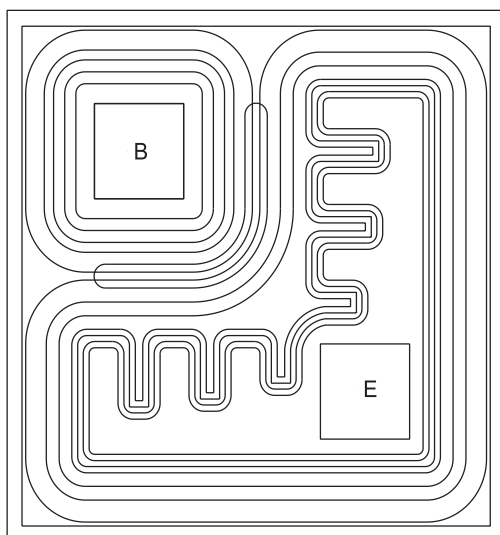


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	26.8 x 26.8 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	4.2 x 4.2 MILS
Emitter Bonding Pad Area	4.3 x 4.3 MILS
Top Side Metalization	Al -
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR

R0

GROSS DIE PER 4 INCH WAFER

15,900

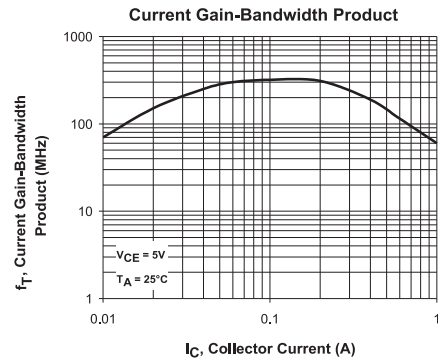
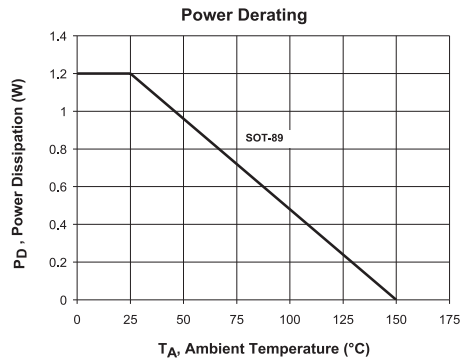
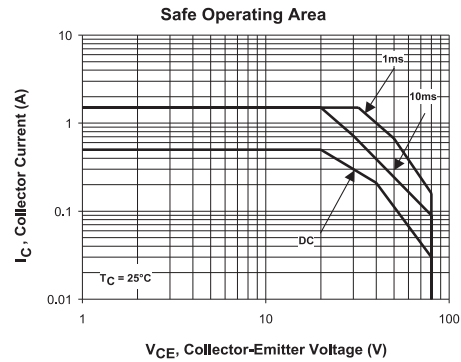
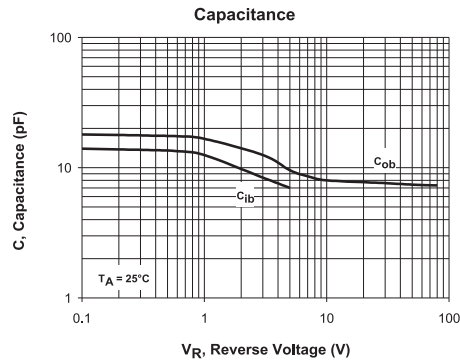
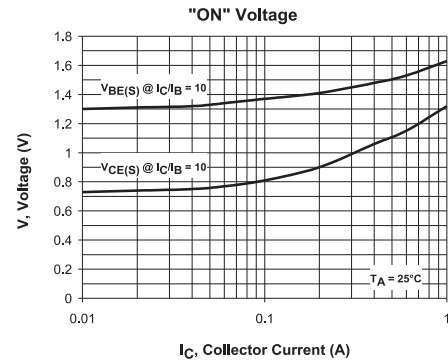
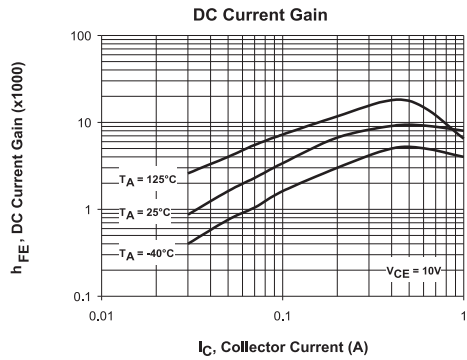
PRINCIPAL DEVICE TYPES

BSS52

BST52

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